

6-5-02 03
R. And A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

RENERUS A. VAN DEN HEUVEL

NL 000674

Serial No.

Filed: CONCURRENTLY

METHOD FOR THE MANUFACTURE OF A SEMICONDUCTOR DEVICE WITH A
FIELD-EFFECT TRANSISTOR

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination,
please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

3. (Amended) A method as claimed in claim 1, characterised in that at the location of the source region (2) and the drain region (3) the gate oxide layer (4) is provided with an aperture (8,9) and that at the location of the aperture (8,9) the gate electrode (1) and the source region (2) and the drain region (3) are provided with a metal layer (11), which with the aid of the underlying silicon is converted into a silicide layer (11).

4. (Amended) A method as claimed in claim 1, characterised in that the distance from the drain region (3) to the gate electrode (1) is chosen between 1 and 4 μm .